MSKSEMI 美森科







TVC



TCC



MOV



GDT



PIFF

BTA12-XXXB(MS)

Product specification





DESCRIPTION

The BTA12-XXXB(MS) series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.

MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	12	А
VDRM /VRRM	600/800	V

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking		
M.S.I.G.I.M.	T2(2) T1(1)	MSKSEMI BAT12-600B MS XXX	MSKSEMI BAT12-800B MS XXX	
2 3		BTA12-600B(MS)	BTA12-800B(MS))	

Notes :XXX represents the order code.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit	
Storage junction temperature range		T _{stg}	-40-150	$^{\circ}$
Operating junction temperature rar	nge	Tj	-40-125	$^{\circ}$ C
Repetitive peak off-state voltage (Γj= 25 ℃)	VDRM	600/800	V
Repetitive peak reverse voltage (T	j=25°C)	VRRM	600/800	V
Non repetitive surge peak Off-state	e voltage	VDSM	V _{DRM} +100	V
Non repetitive peak reverse voltag	е	VRSM	V _{RRM} +100	V
RMS on-state current(TC=85℃)		I _{T(RMS)}	12	А
Non repetitive surge peak on-state current (full cycle, F=50Hz)		Ітѕм	120	А
Pt value for fusing (tp=10ms)		l²t	78	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT})		dl/dt	50	A/µs
Peak gate current		lдм	4	Α
Average gate power dissipation		P _{G(AV)}	1	W
Peak gate power		P _{GM}	5	W



ELECTRICAL CHARACTERISTICS (T_j=25 °C unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit			
lgт	V 40V D 000	I - II-III	MAX	50	mA			
V _{GT}	V _D =12V R _L =33Ω	I - II-III	MAX	1.3	V			
V _{GD}	$V_D = V_{DRM} T_j = 125^{\circ}C$ RL = 3.3K Ω	I - II-III	MIN	0.2	V			
			I - I - I - I - I	I -III	B 4 A X /	80	•	
lL	lg =1.2Igт	II		MAX	90	mA		
lн	lτ =100mA		MAX	60	mA			
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125℃		MIN	1000	V/µs			
(dl/dt)c	Without snubber T _j =	=125 ℃	MIN	12	A/ms			

4 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit	
		I - II-III	B 4 A X C	50		
lgт	V _D =12V R _L =33Ω	IV	MAX	70	mA	
V _{GT}		ALL	MAX	1.3	V	
V _{GD}	$V_D = V_{DRM} T_j = 125^{\circ}C R_L$ =3.3K Ω	ALL	MIN	0.2	V	
		I -III-IV		50		
lь		II	MAX	100	mA	
lн	h =100mA		MAX	50	mA	
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125℃		MIN	500	V/µs	
(dV/dt)c	$(dI/dt)c=5.3A/ms$ $T_j=$	125 ℃	MIN	10	V/µs	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
Vтм	I _{TM} =17Atp=380μs		1.5	V
IDRM	VD =VDRM VR =VRRM	T _j =25℃	5	μA
IRRM	VD - VDRIM VR - VRRIM	T _j =125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-c)	junction to case(AC)	2.3	°C /W



FIG.1 Maximum power dissipation versus RMS on-state current

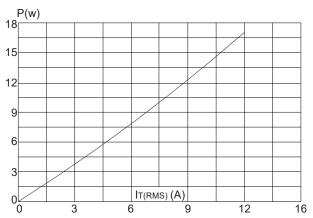


FIG.2: RMS on-state current versus case temperature

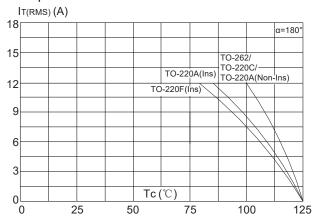


FIG.3: Surge peak on-state current versus number of cycles

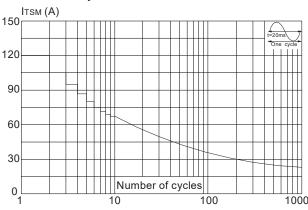


FIG.4: On-state characteristics (maximum values)

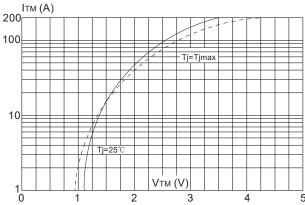


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (dI/dt(I-I-II) < 50A/ μ s)

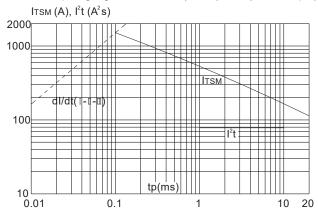
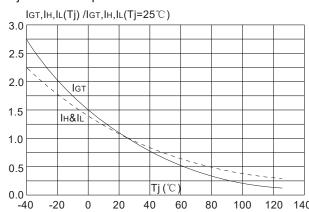
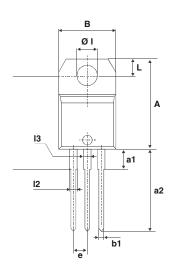


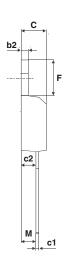
FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature





PACKAGE MECHANICAL DATA





	DIMENSIONS					
REF.	Millimete		ers		Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
В	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
С	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
е	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
ØI	3.75		3.85	0.147		0.151
14	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
12	1.14		1.70	0.044		0.066
13	1.14		1.70	0.044		0.066
М		2.60			0.102	

REEL SPECIFICATION

P/N	PKG	QTY
BTA12-XXXB(MS)	TO-220	50/One tube 1000/a box of



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